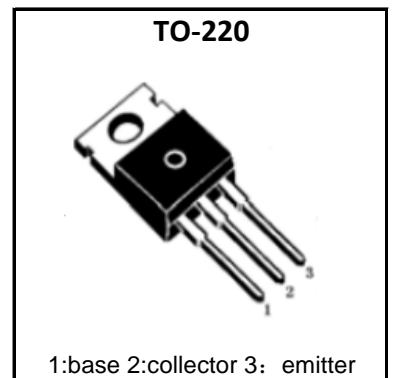


**TIP32C**

**FEATURES**

Medium Power Linear Switching Applications  
Complementary to TIP31C

Silicon PNP triode



**Maximum ratings(Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	-100	V
Collector-Emitter Voltage	VCEO	-100	V
Emitter-Base Voltage	VEBO	-5	V
Collector Current — Continuous	IC	-3	A
Collector Power Dissipation	Pc	2	W
Junction Temperature	TJ	150	°C
Storage Temperature	Tstg	-55~150	°C

**Electrical Characteristics (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-Base breakdown voltage	VCBO	IC=-1mA IB=0	-100		V
Collector-Emitter Sustaining Voltage	VCEO(SUS)	IC=30mA IB=0	-100		V
Emitter-Base Breakdown Voltage	VEBO	IE=1mA IC=0	-5		V
Collector Cutoff Current	ICBO	VCB=100V IE=0		-0.2	mA
Collector Cutoff Current	ICEO	VCE=60V IB=0		-0.3	mA
Emitter Cutoff Current	IEBO	VEB=5V IC=0		-1	mA
DC Current Gain	hFE	VCE=-4V IC=-1A	25		
		VCE=-4V IC=-3A	15	75	
Collector-Emitter Saturation Voltage	VCE(sat)	IC=-3A IB=-375mA		-1.2	V
Base-emitter voltage	VBE(on)	IC=-3A VCE=-4V		-1.8	V
Transition frequency	fT	VCE=-10V , IC=-0.5A	3		MHz